

isc N-Channel MOSFET Transistor

STF10NM60ND

• FEATURES

- Drain-source on-resistance:
 $R_{DS(on)} \leq 0.6\Omega$ (max)
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

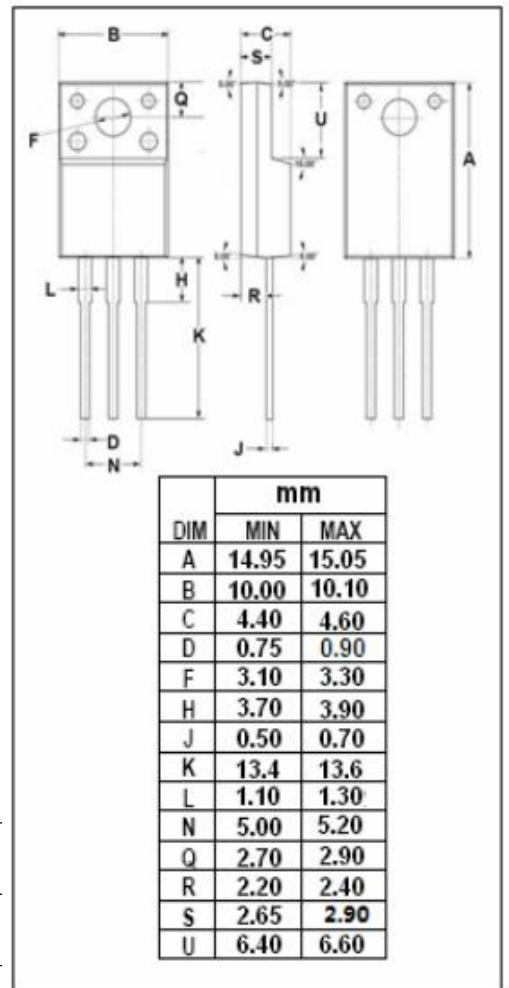
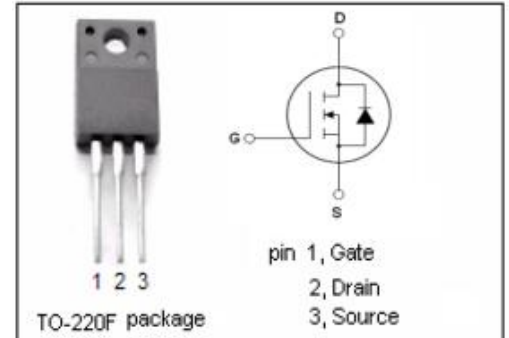
- Reliable device for use in a wide variety of applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 25	V
I_D	Drain Current-Continuous	8	A
I_{DM}	Drain Current-Single Pulsed	32	A
P_D	Total Dissipation @ $T_c=25^\circ\text{C}$	25	W
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	5	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 1mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =250uA	3		5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =4A			0.6	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 25V; V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μ A
V _{SD}	Diode forward voltage	I _{DR} =8A, V _{GS} = 0 V			1.5	V
T _{rr}	Reverse recovery time	ISD=8A, di/dt=100A/us		118	200	nS

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